

AMENDMENTS TO THE ABSTRACT

Please replace the following substitute abstract for the abstract currently on file:

The present invention relates to a composition for forming a low dielectric insulating film for a semiconductor device, particularly to an organosilicate polymer prepared by mixing a thermally decomposable organic silane compound that is capped with a silane compound at both its ends, and a common silane compound or silane oligomer, and then adding water and a catalyst to conduct hydrolysis and condensation, as well as to a coating composition for an insulating film for a semiconductor device comprising the same, a coating composition for an insulating film for a semiconductor device further comprising a pore-forming organic substance, a method for preparing an insulating film for a semiconductor device by coating the composition and curing, and a semiconductor device comprising a low dielectric insulating film prepared by the method.